TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

HN1B04FU

Audio Frequency General Purpose Amplifier Applications

Q1:High voltage and high current

 $: V_{CEO} = 50V, I_{C} = 150mA (max)$

• High h_{FE}: $h_{FE} = 120 \sim 400$

• Excellent hfe linearity

 $: h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (typ.)}$

Q2:

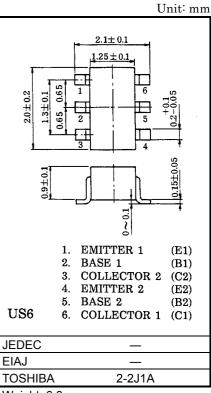
• High voltage and high current

 $V_{CEO} = -50V, I_{C} = -150 \text{mA (max)}$

• High h_{FE} : $h_{FE} = 120 \sim 400$

Excellent hfe linearity

 $: h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 \text{ (typ.)}$

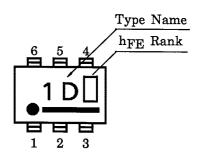


Weight: 6.8mg

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	٧
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	150	mA
Base current	ΙΒ	30	mA

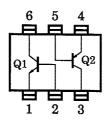
Marking



Q2 Maximum Ratings (Ta = 25°C)

Equivalent Circuit (Top View)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	٧
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ic	-150	mA
Base current	Ι _Β	-30	mA



Q1,Q2 Common Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

^{*} Total rating

Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 60V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	_	$V_{EB} = 5V, I_{C} = 0$	_	_	0.1	μΑ
DC current gain	h _{FE (Note)}	_	V _{CE} = 6V, I _C = 2mA	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	_	0.1	0.25	٧
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 1mA	_	150	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	-	2	_	pF

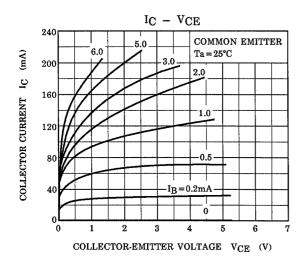
Q2 Electrical Characteristics (Ta = 25°C)

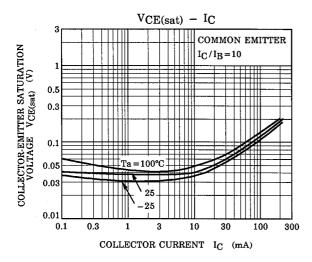
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V, I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	_	V _{EB} = -5V, I _C = 0	_	_	-0.1	μA
DC current gain	h _{FE (Note)}	_	$V_{CE} = -6V, I_{C} = -2mA$	120	-	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -100mA, I _B = -10mA	_	-0.1	-0.3	V
Transition frequency	f _T	_	V _{CE} = −10V, I _C = −1mA	_	120	_	MHz
Collector output capacitance	C _{ob}	_	$V_{CB} = -10V, I_{E} = 0,$ f = 1MHz	_	4	_	pF

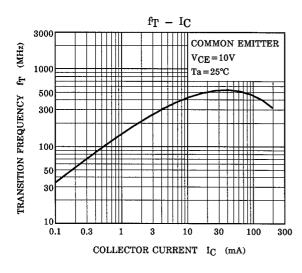
Note: hfe Classification Y (Y): 120~240, GR (G): 200~400

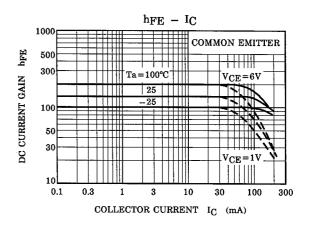
() Marking Symbol

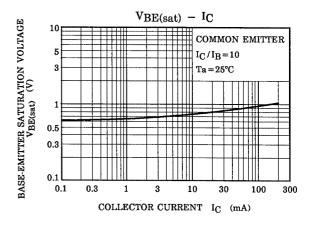
Q1 (NPN transistor)

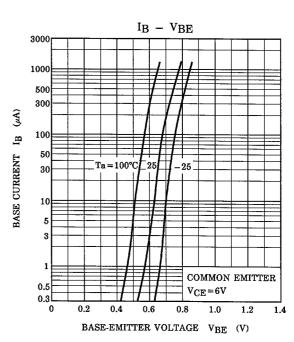






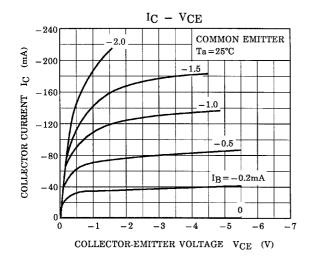


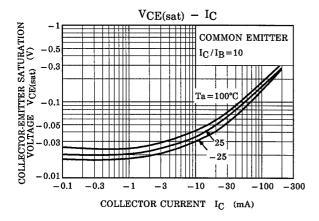


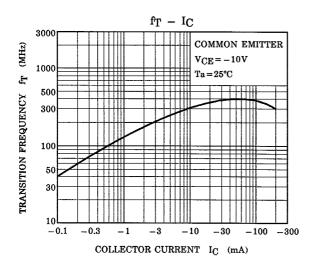


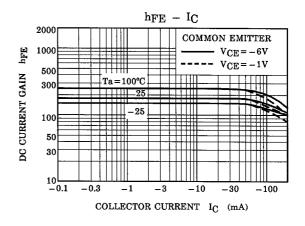
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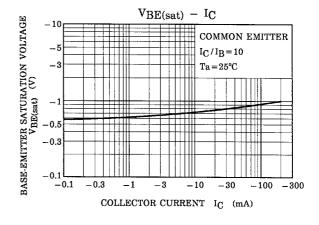
Q2 (PNP transistor)

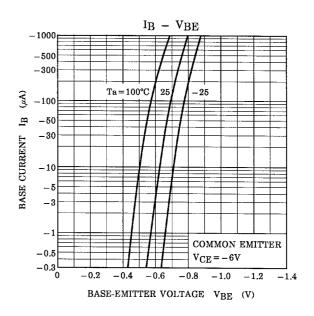




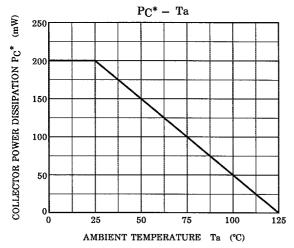








(Q1, Q2 Common)



*: Total Rating

5

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